

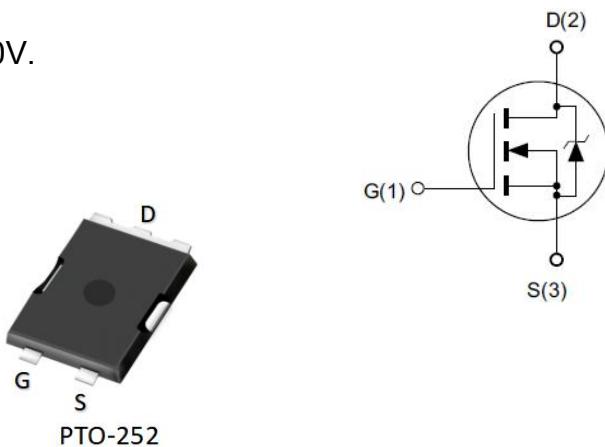


# MPP12N65

## N-Channel Power MOSFET

### Features

- ◆ 650V, 12A,  $R_{DS(ON)}$ (Typ.) = 0.65Ω@VGS = 10V.
- ◆ Low Crss
- ◆ Fast Switching
- ◆ 100% Avalanche Tested



### Application

- ◆ Adapter
- ◆ LCD Panel Power
- ◆ E-Bike Charger
- ◆ Switching Mode Power Supply

### Absolute Maximum Ratings $T_c = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Limit	Unit
		PTO-252	
$V_{DS}$	Drain-Source Voltage <sup>a</sup>	650	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-Continuous, $T_c = 25^\circ C$	12	A
	Drain Current-Continuous, $T_c = 100^\circ C$	7.5	A
$I_{DM}$	Drain Current-Pulsed <sup>b</sup>	48	A
$P_D$	Maximum Power Dissipation @ $T_J = 25^\circ C$	120	W
EAS	Single Pulsed Avalanche Energy <sup>d</sup>	500	mJ
$T_J, T_{STG}$	Operating and Store Temperature Range	-55 to 150	°C

### Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-Case Max.	1.04	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient Max.	62.5	°C/W

### Electrical Characteristics $T_J = 25^\circ C$ unless otherwise noted

#### Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	650	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V$	-	-	1	μA
$I_{GSS}$	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	$\pm 100$	nA



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## ■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	2	-	4	V
$R_{DS(\text{on})}$	Static Drain-Source On-Resistance <sup>c</sup>	$V_{GS} = 10\text{V}$ , $I_D = 6\text{A}$	-	0.65	0.80	$\Omega$

## ■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1.0\text{MHz}$	-	1780	-	pF
$C_{oss}$	Output Capacitance		-	162	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	9.6	-	pF

## ■ On Characteristics

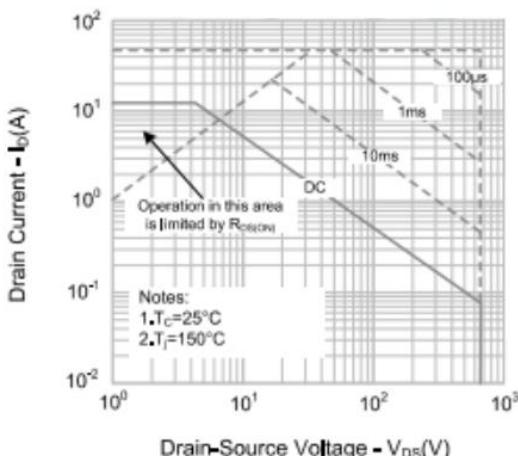
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 325\text{V}$ , $I_D = 12\text{A}$ , $R_G = 10\Omega$ , $V_{GS}=10\text{V}$	-	29	-	ns
$t_r$	Turn-On Rise Time		-	27	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	65	-	ns
$t_f$	Turn-Off Fall Time		-	46	-	ns
$Q_g$	Total Gate Charge	$V_{DS} = 520\text{V}$ , $I_D = 12\text{A}$ , $V_{GS} = 10\text{V}$	-	40.2	-	nC
$Q_{gs}$	Gate-Source Charge		-	10.3	-	nC
$Q_{gd}$	Gate-Drain Charge		-	14.4	-	nC

## ■ Drain-Source Diode Characteristics

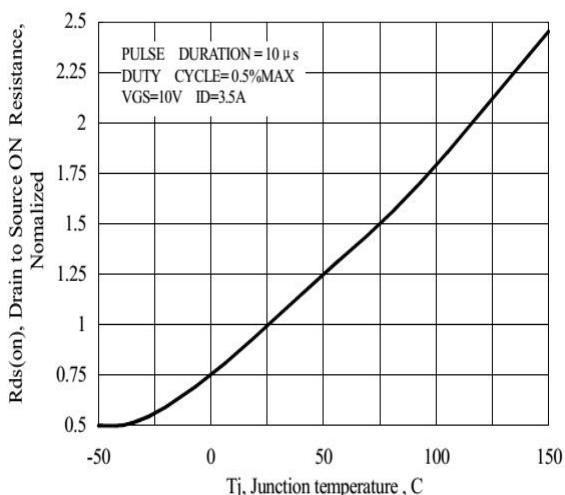
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$I_s$	Drain-Source Diode Forward Continuous Current	$V_{GS} = 0\text{V}$	-	-	12	A
$I_{SM}$	Maximum Pulsed Current	$V_{GS} = 0\text{V}$	-	-	48	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_s = 12\text{A}$	-	-	1.5	V
$trr$	Reverse Recovery Time	$I_s=12\text{A}$ , $T_j = 25^\circ\text{C}$ $dI/dt=100\text{A}/\mu\text{s}$ , $V_{GS}=0\text{V}$	-	650	-	ns
$Qrr$	Reverse Recovery Charge		-	4.29	-	nC

Notes:

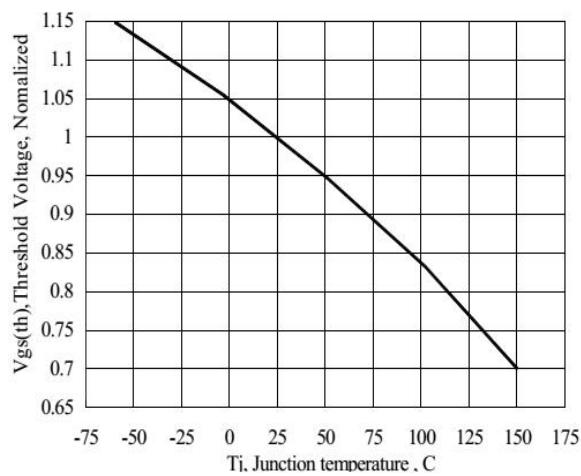
- a.  $T_j = +25^\circ\text{C}$  to  $+150^\circ\text{C}$
- b. Repetitive rating; pulse width limited by maximum junction temperature.
- c. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$
- d.  $L=10\text{mH}$ ,  $V_{DD}=50\text{V}$ ,  $I_{as}=10\text{A}$ ,  $R_G=25\Omega$  Starting  $T_j=25^\circ\text{C}$



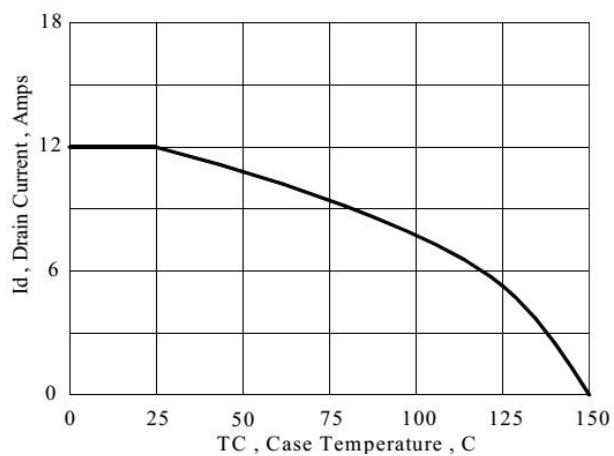
**Figure 1. Maximum Safe Operating Area**



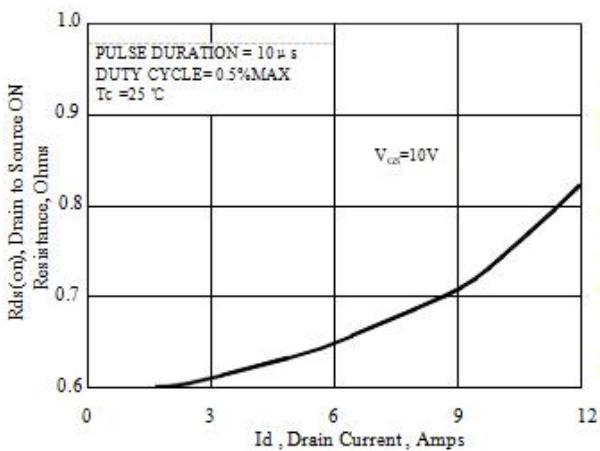
**Figure 2. Normalized On-Resistance Variation with Temperature**



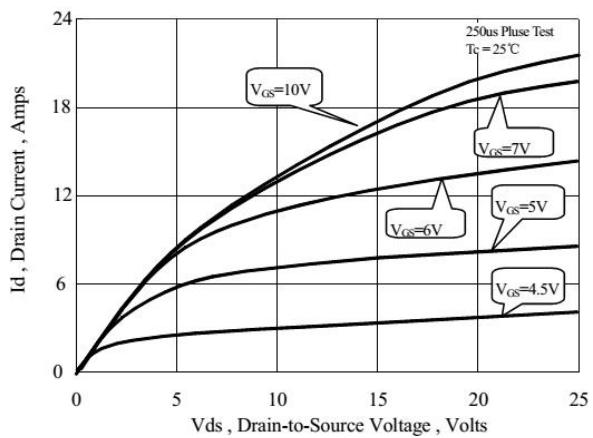
**Figure 3. Gate Threshold Variation with Temperature**



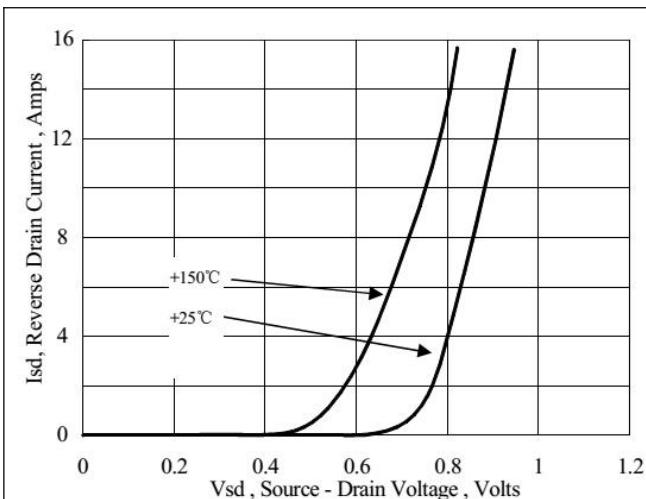
**Figure 4. Maximum Drain Current with Case Temperature**



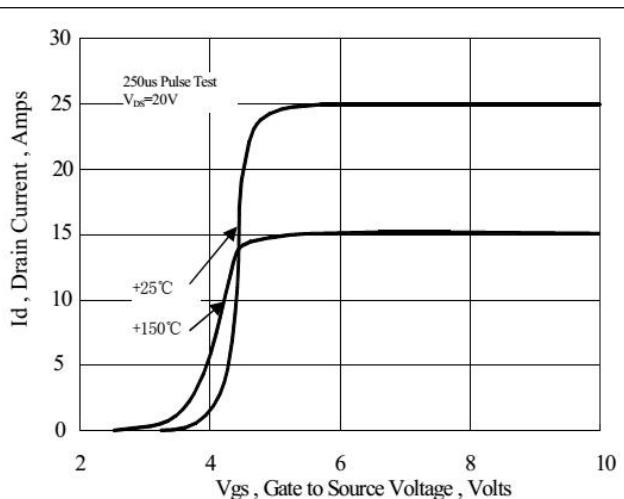
**Figure 5. Typical Drain to Source ON Resistance vs Drain Current**



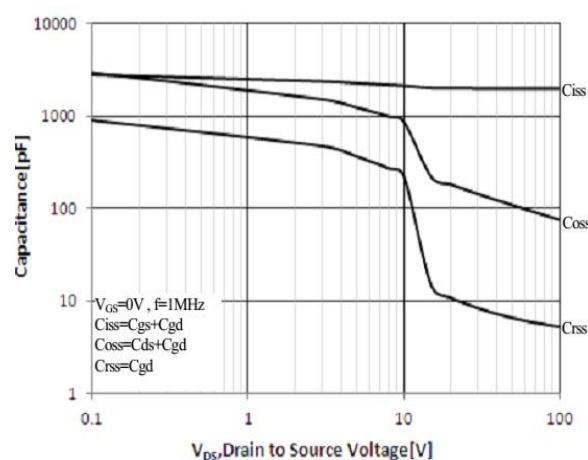
**Figure 6. On-State Characteristics**



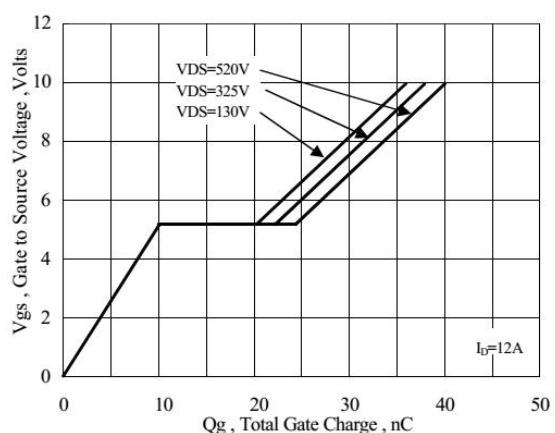
**Figure 7.** Body Diode Forward Voltage Variation with Source Current



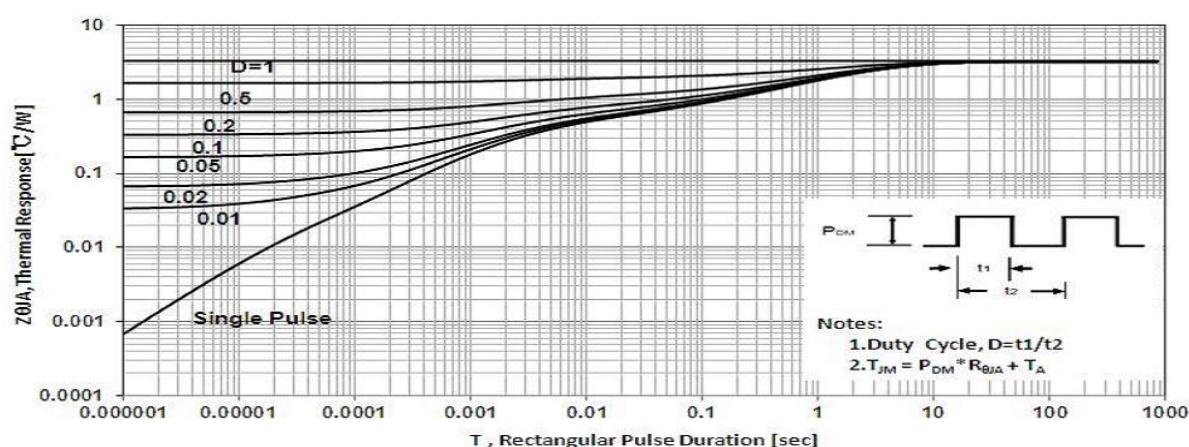
**Figure 8.** Transfer Characteristics Variation with Source Current



**Figure 9.** Capacitance Characteristics

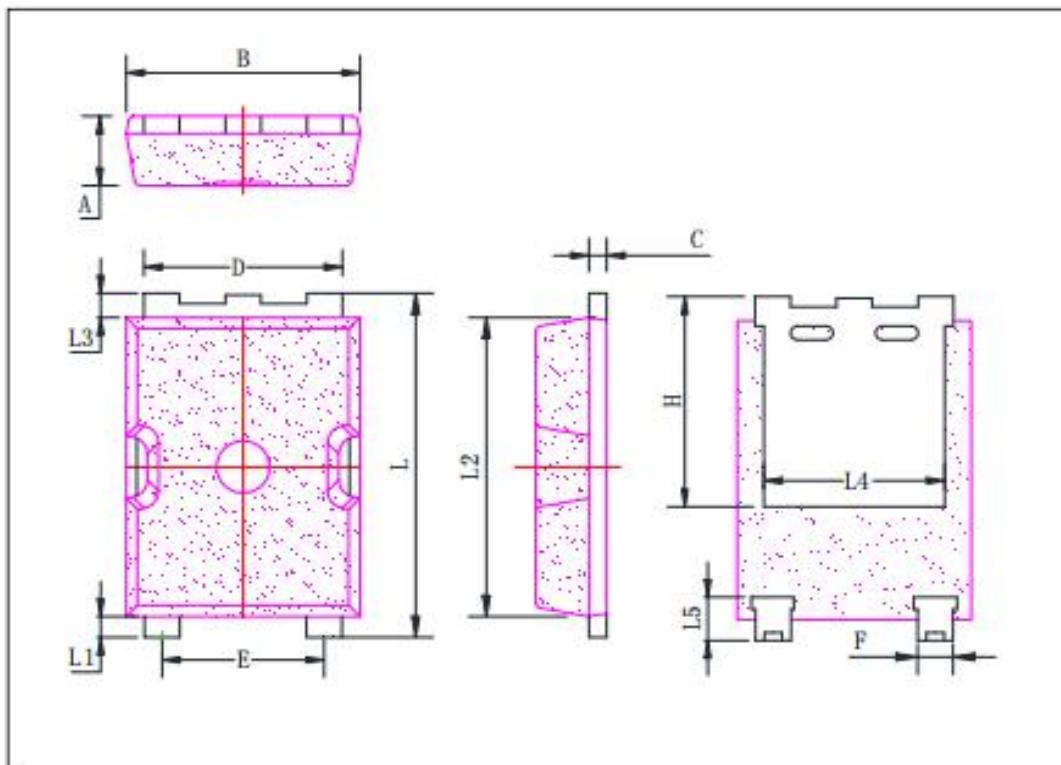


**Figure 10.** Gate Charge Characteristics



**Figure 11.** Normalized Effective Transient Thermal Impedance With Pulse Duration

## ■ Package Information



Symbol	Min	Typ	Max
A	1.90	2.00	2.10
B	6.50	6.60	6.70
C	0.45	0.50	0.60
D	5.50	5.60	5.70
E	4.50	4.60	4.70
F	0.90	1.00	1.05
H	5.90	6.05	6.20
L	9.80	9.90	10.0
L1	0.50	0.60	0.70
L2	8.50	8.60	8.70
L3	0.60	0.70	0.80
L4	4.65	4.80	4.90
L5	1.10	1.25	1.40